

Fig. 10.1 (a) The gate-controlled diode structure.  
 (b) Idealized representation of the portion of the surface enclosed by the dashed frame in (a).<sup>1</sup>

A. S. Grove, "Phys. & Techn. of Semi. Dev.," Wiley, 1967, p. 290.

Case II

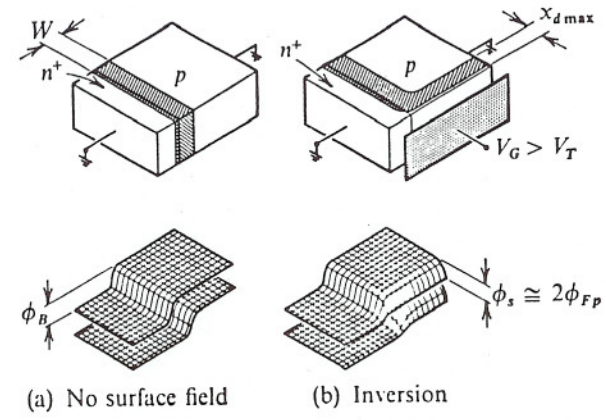


Fig. 10.2 p-n Junction under the influence of surface fields—equilibrium case ( $V_J = 0$ ).<sup>1</sup>

Case III

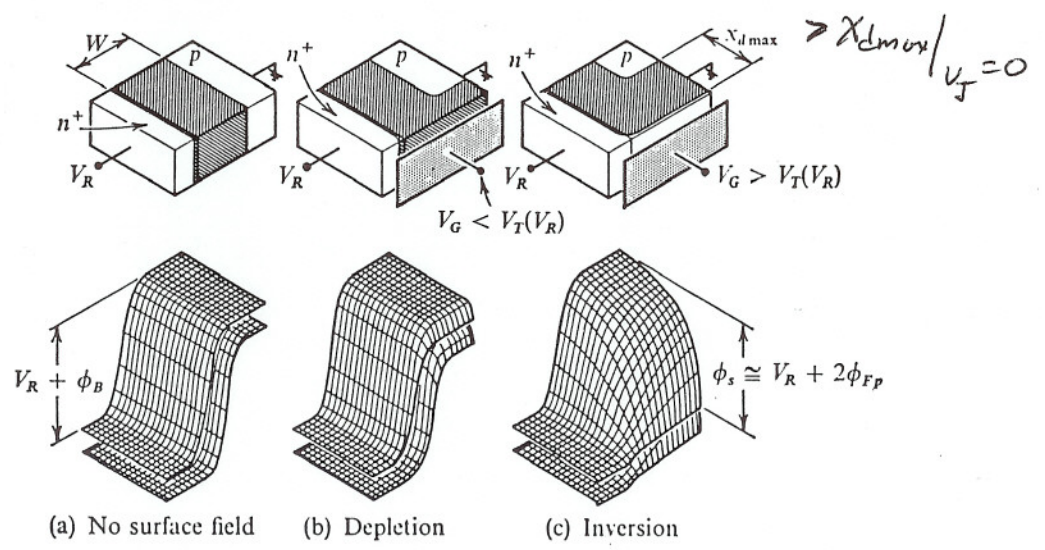


Fig. 10.3 p-n Junction under the influence of surface fields—reverse bias case ( $V_J = V_R > 0$ ).<sup>1</sup>

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